

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^d	Q _g (Typ.)
- 30	0.005 at V _{GS} = - 10 V	- 29	61 nC
	0.00775 at V _{GS} = - 4.5 V	- 23	

FEATURES

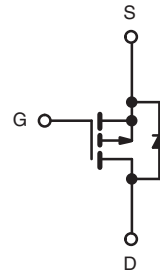
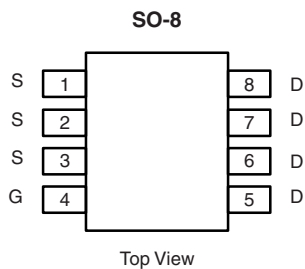
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Adaptor Switch
- Notebook



Ordering Information: Si4459ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 29
		T _C = 70 °C	- 23.5
		T _A = 25 °C	- 19.7 ^{a, b}
		T _A = 70 °C	- 15.6 ^{a, b}
Pulsed Drain Current	I _{DM}	- 70	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 2.9 ^{a, b}
Avalanche Current	I _{AS}	- 30	mJ
Single-Pulse Avalanche Energy	E _{AS}	45	
Maximum Power Dissipation	P _D	T _C = 25 °C	7.8
		T _C = 70 °C	5
		T _A = 25 °C	3.5 ^{a, b}
		T _A = 70 °C	2.2 ^{a, b}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c}	R _{thJA}	29	35	°C/W	
Maximum Junction-to-Foot	R _{thJF}	13	16		

Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 80 °C/W.
- Based on T_C = 25 °C.

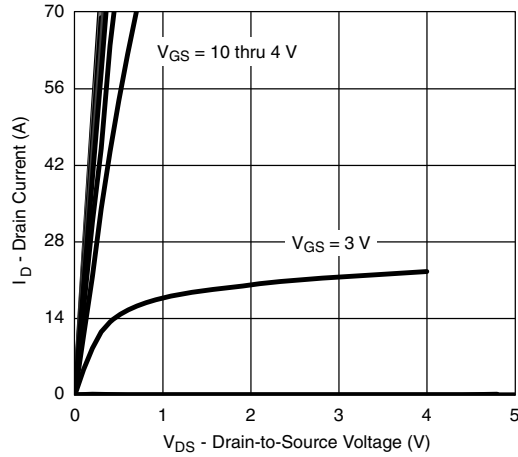
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 30			V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 31		mV/°C	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		5.3				
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 2.5	V	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			- 100		
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			- 75		
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 75\text{ }^\circ\text{C}$			- 10		μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 75\text{ }^\circ\text{C}$			- 3		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}, V_{GS} = -10\text{ V}$	- 30			A	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -15\text{ A}$		0.0039	0.005	Ω	
		$V_{GS} = -4.5\text{ V}, I_D = -10\text{ A}$		0.0062	0.00775		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -15\text{ A}$		24		S	
Dynamic^b							
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		6000		pF	
Output Capacitance	C_{oss}		860				
Reverse Transfer Capacitance	C_{rss}		790				
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		129	195	nC	
				61	95		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		16.5			
Gate-Drain Charge	Q_{gd}		23.5				
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.6	3	6	Ω	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		16	30	ns	
Rise Time	t_r		16	30			
Turn-Off Delay Time	$t_{d(off)}$		80	150			
Fall Time	t_f		20	40			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		75	150		
Rise Time	t_r		130	260			
Turn-Off Delay Time	$t_{d(off)}$		60	120			
Fall Time	t_f		40	80			
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 29	A	
Pulse Diode Forward Current	I_{SM}				- 70		
Body Diode Voltage	V_{SD}	$I_S = -3\text{ A}, V_{GS} = 0\text{ V}$		- 0.71	- 1.2	V	
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		67	130	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		74	150	nC		
Reverse Recovery Fall Time	t_a		22		ns		
Reverse Recovery Rise Time	t_b		45				

Notes:

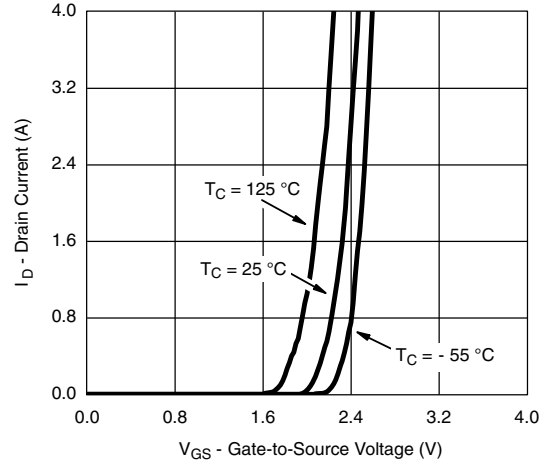
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

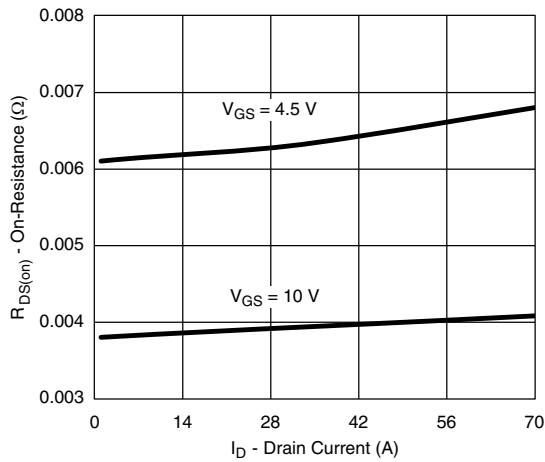
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



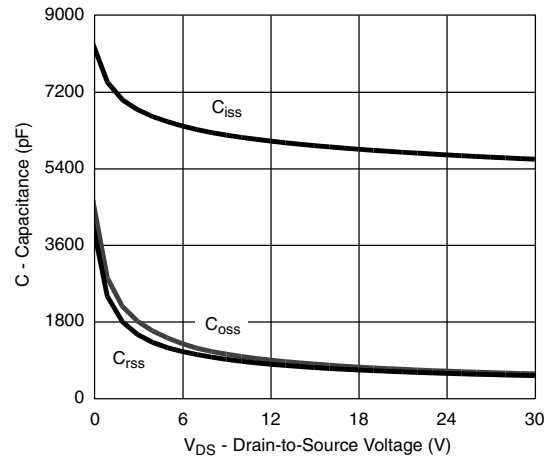
Output Characteristics



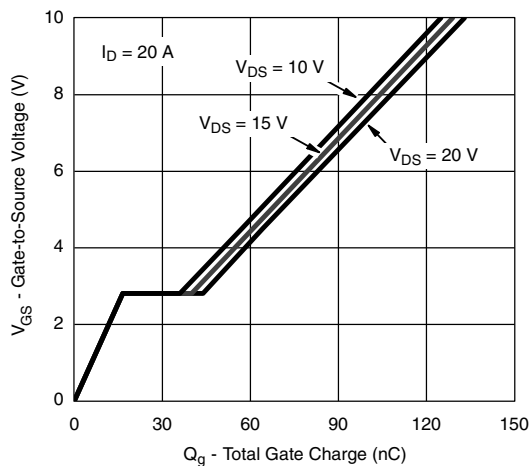
Transfer Characteristics



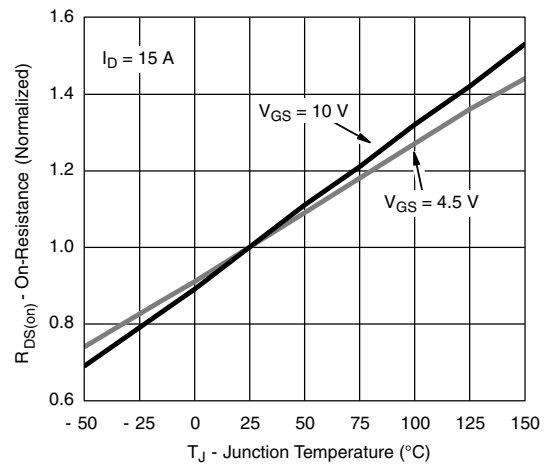
On-Resistance vs. Drain Current



Capacitance

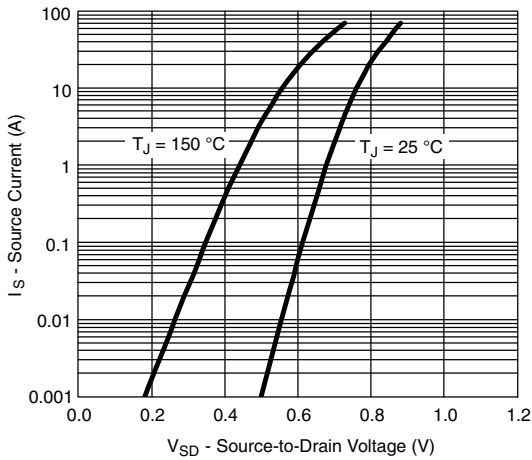


Gate Charge

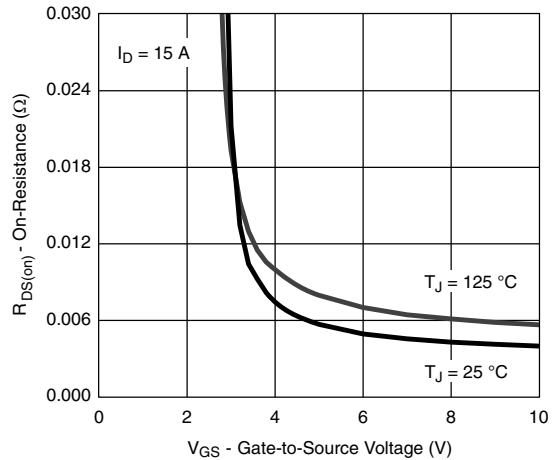


On-Resistance vs. Junction Temperature

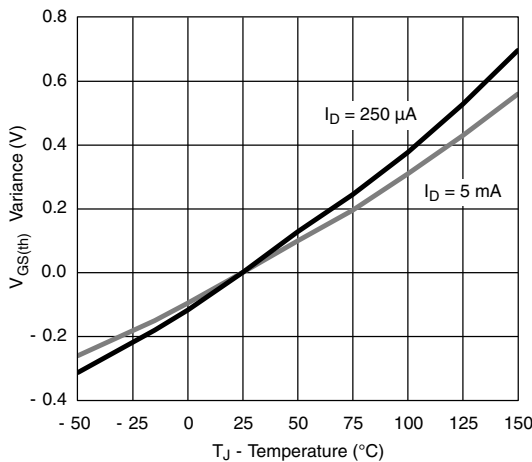
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



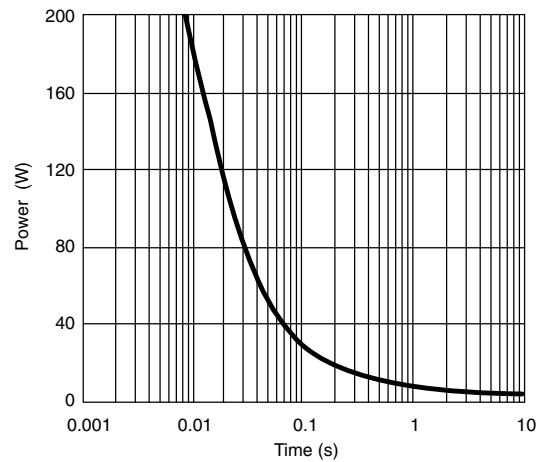
Source-Drain Diode Forward Voltage



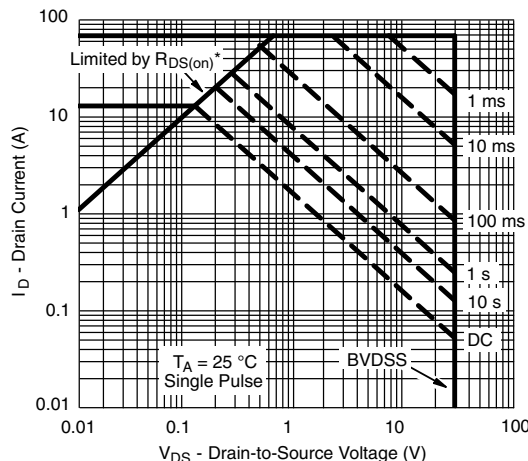
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



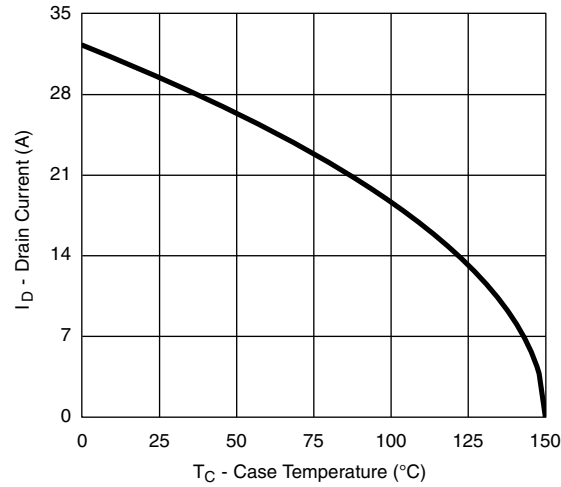
Single Pulse Power, Junction-to-Ambient



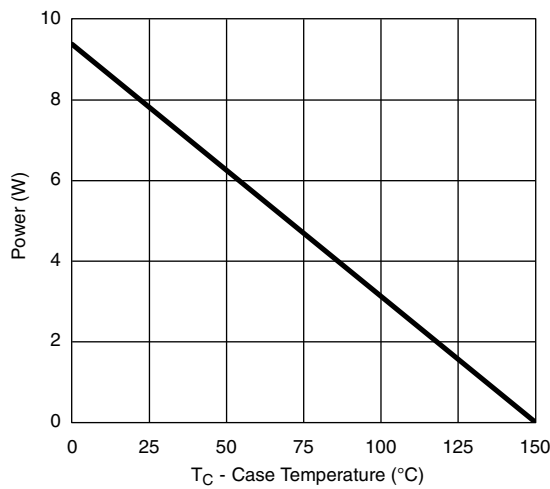
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

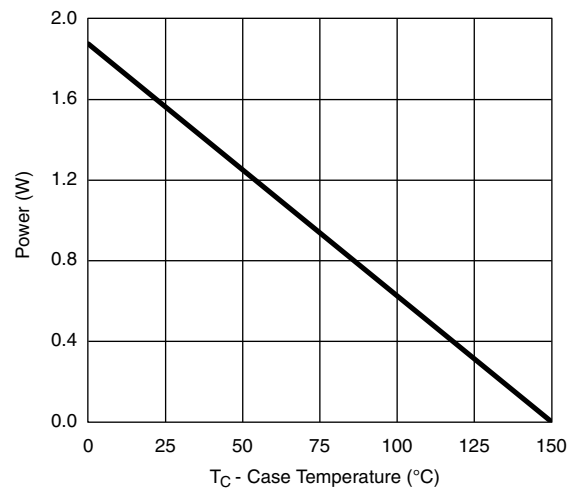
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



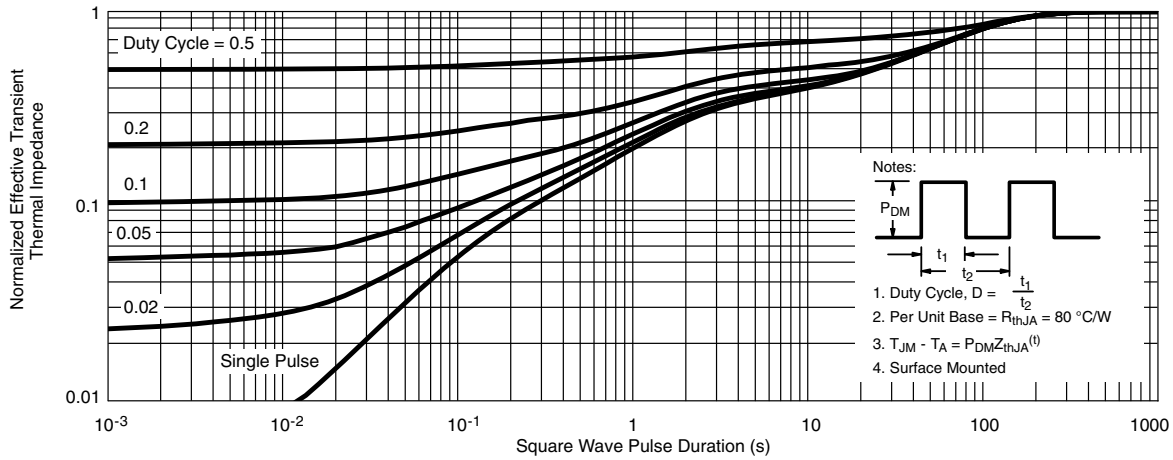
Power, Junction-to-Foot



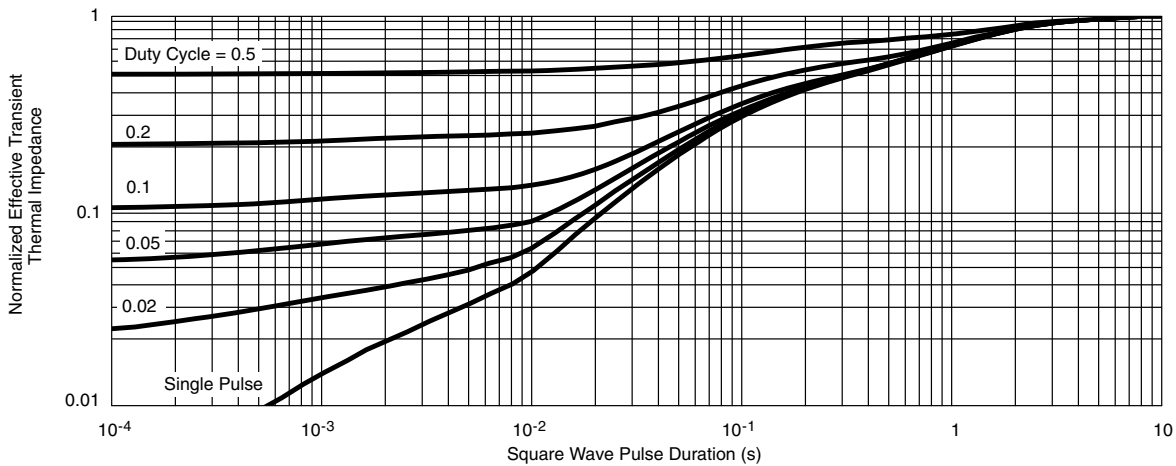
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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